Silicon NPN Power Transistors BU2520D

DESCRIPTION

·With TO-3PN package
·High voltage,high speed
·Built-in damper diode

APPLICATIONS

·For use in horizontal deflection circuits of large screen colour TV receivers.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

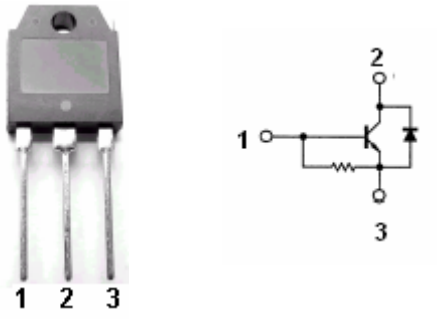

Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	7.5	V
I_C	Collector current (DC)		10	A
I_{CM}	Collector current-peak		25	A
I_B	Base current(DC)		6	A
I_{BM}	Base current-peak		9	A
P_C	Collector power dissipation	T_C=25□	125	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-65~150	□

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=100mA ;I_B=0,L=25mH	800			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_B=600mA; I_C=0	7.5	13.5		V
V_{CEsat}	Collector-emitter saturation voltage	I_C=6A; I_B=1.2A			5.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=6A; I_B=1.2A			1.3	V
I_{CES}	Collector cut-off current	V_{CE}=ratedV_{CE}; V_{BE}=0 T_j=125□			1.0 2.0	mA
I_{EBO}	Emitter cut-off current	V_{EB}=7.5V; I_C=0	100		300	mA
h_{FE-1}	DC current gain	I_C=1A ; V_{CE}=5V			23	
h_{FE-2}	DC current gain	I_C=6A ; V_{CE}=5V	5	7	10	
V_F	Diode forward voltage	I_F=6A			2.2	V
C_C	Collector capacitance	I_E=0 ;V_{CB}=10V;f=1MHz		115		pF

PACKAGE OUTLINE

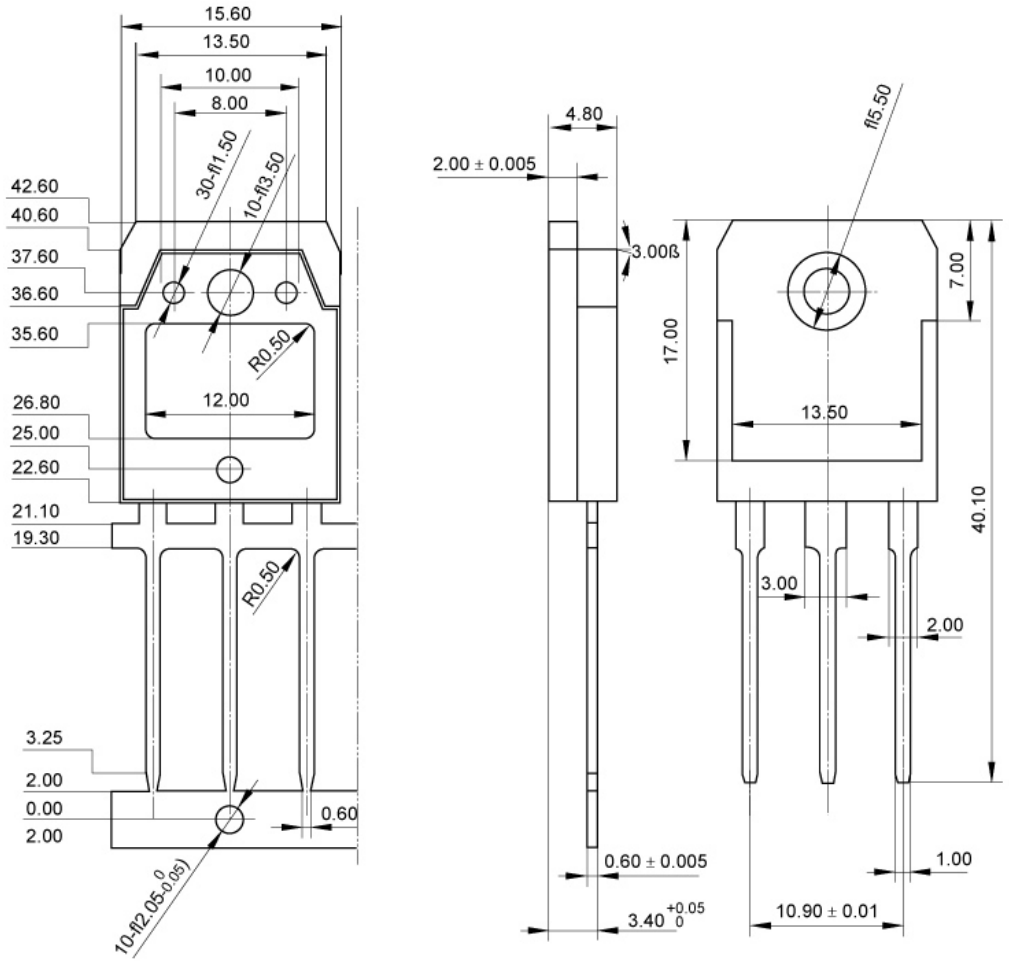

Fig.2 outline dimensions (unindicated tolerance:±0.10 mm)